

Indian Institute of Technology Guwahati Research and Development Section Guwahati-781039, Assam

Applications are invited for an **Online interview** for the following post(s) in the ANRF-funded project entitled "**Development of a state-of-the-art single crystal growth facility for high-purity quantum material synthesis**" at the Department of Physics, IIT Guwahati.

Date: 15th July 2025 (Tuesday)

Time: From 10.00 AM onwards.

Online Interview: A link will be provided to the shortlisted candidates.

Sl. No.	Project Staff Designation	Number of Vacancies	Pay Recommended (Rs.)	HRA (Rs.)	Medical Required (Rs.)	Total Amount (Rs.)	Duration of Appointment in months	Qualifications
1	JRF (GATE)	1	37000	7400	N/A	44400	08	M.Sc / MS or equivalent degree in Physics. The candidate must be GATE or CSIR-UGC NET qualified. The priority will be given to candidates having prior research experience in experimental condensed matter physics/material science.

How to apply and selection process: Interested candidates must submit their CV including details of all educational qualifications, experience, contact address, phone number, email, etc. Candidates also must submit photocopies of relevant documents in <u>a single PDF file</u> only containing all the documents (i.e. mark sheets, copy of the degree certificates, work experience certificates, caste certificate etc.) at the email address <u>rsingha@iitg.ac.in</u> by 11th July 2025 before 5 PM having a subject line "Application for the post of JRF (GATE) in the ANRF project". After 11th July 2025, 5 PM, the application will not be considered. Candidates will be shortlisted based on the qualifications posted in the advertisement, and only shortlisted candidates will be invited by email to attend an online interview on 15th July 2025 from 10 am.

Selection will be based on the performance of the candidate in the interview. For any clarification, contact: Dr. Ratnadwip Singha (Principal Investigator) Email: rsingha@iitg.ac.in Phone: 0361-2583654.

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